2SK2144

Silicon N-Channel MOS FET

HITACHI

Application

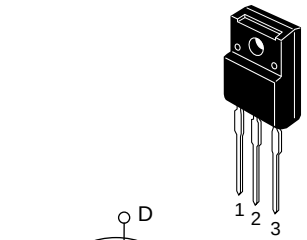
High speed power switching

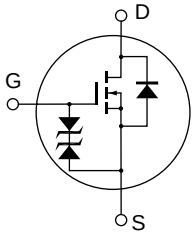
Features

- Low on-resistance
- High speed switching
- Low drive current
- No Secondary Breakdown
- Suitable for Switching regulator, DC-DC converter

Outline

TO-220CFM





1. Gate
2. Drain
3. Source

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Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	600	V
Gate to source voltage	V_{GSS}	±30	V
Drain current	I_D	3	A
Drain peak current	$I_{D(pulse)}$*[1]	6	A
Body to drain diode reverse drain current	I_{DR}	3	A
Channel dissipation	Pch*[2]	25	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	–55 to +150	°C

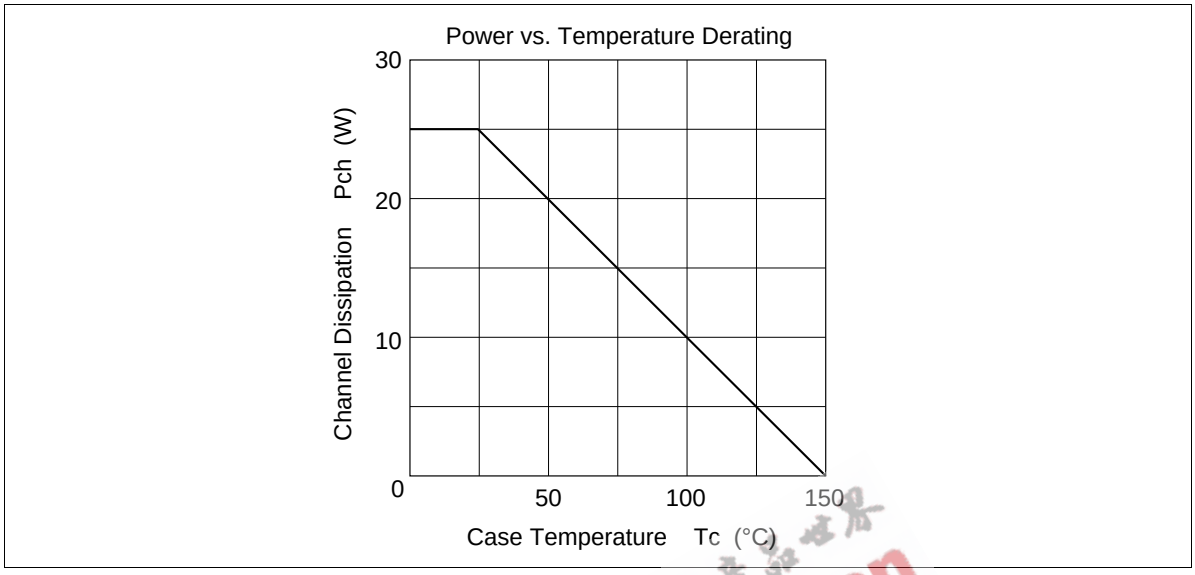
Notes 1. PW ≤ 10 µs, duty cycle ≤ 1 %
2. Value at Tc = 25 °C

Electrical Characteristics (Ta = 25°C)

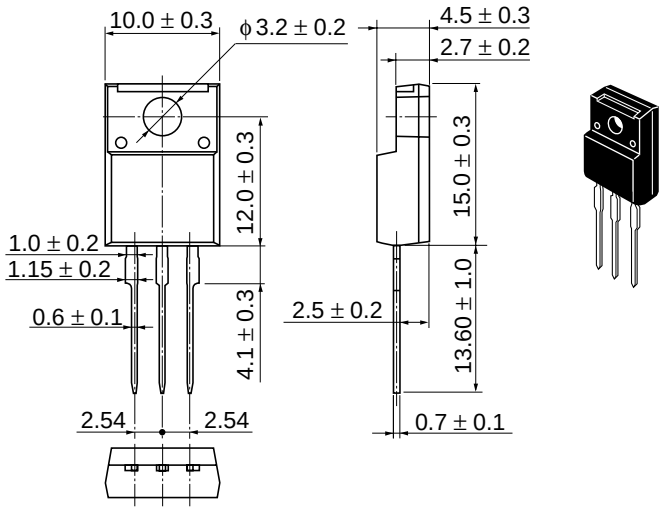
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	600	—	—	V	I_D = 10 mA, V_{GS} = 0
Gate to source breakdown voltage	$V_{(BR)GSS}$	±30	—	—	V	I_G = ±100 µA, V_{DS} = 0
Gate to source leak current	I_{GSS}	—	—	±10	µA	V_{GS} = ±25 V, V_{DS} = 0
Zero gate voltage drain current	I_{DSS}	—	—	250	µA	V_{DS} = 500 V, V_{GS} = 0
Gate to source cutoff voltage	$V_{GS(off)}$	2.0	—	3.0	V	I_D = 1 mA, V_{DS} = 10 V
Static drain to source on state resistance	$R_{DS(on)}$	—	3.8	5.0	Ω	I_D = 1 A V_{GS} = 10 V*[1]
Forward transfer admittance	$\|y_{fs}\|$	1.2	2.0	—	S	I_D = 1 A V_{DS} = 10 V*[1]
Input capacitance	Ciss	—	295	—	pF	V_{DS} = 10 V
Output capacitance	Coss	—	70	—	pF	V_{GS} = 0
Reverse transfer capacitance	Crss	—	12	—	pF	f = 1 MHz
Turn-on delay time	$t_{d(on)}$	—	8	—	ns	I_D = 1 A
Rise time	t_r	—	25	—	ns	V_{GS} = 10 V
Turn-off delay time	$t_{d(off)}$	—	65	—	ns	R_L = 30 Ω
Fall time	t_f	—	30	—	ns	
Body to drain diode forward voltage	V_{DF}	—	0.9	—	V	I_F = 2 A, V_{GS} = 0
Body to drain diode reverse recovery time	t_{rr}	—	220	—	ns	I_F = 2 A, V_{GS} = 0, di_F / dt = 100 A / µs

Note 1. Pulse Test

See characteristic curve of 2SK1572.


Power vs. Temperature Derating
Channel Dissipation Pch (W)
30
20
10
0
50
100
150
Case Temperature Tc (°C)

Unit: mm



Hitachi Code	TO-220CFM
JEDEC	—
EIAJ	—
Weight (reference value)	1.9 g

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